

Appl. No. 10/820,856  
Amendment dated: August 11, 2006  
Reply to OA of: May 11, 2006

This listing of claims will replace all prior versions and listings of claims in the application.

**Listing of Claims:**

1(original). An under bump metallization structure applicable to be disposed on bonding pads of a semiconductor wafer, wherein a passivation layer covers the wafer and exposes the bonding pads, the under bump metallization structure comprising:

- an adhesive layer formed on the bonding pads;
- a first barrier layer disposed on the adhesive layer;
- a wetting layer formed on the first barrier layer; and
- a second barrier layer disposed on the wetting layer, wherein a material of the second barrier comprises tin and copper.

2(original). The structure of claim 1, wherein the quantity of the tin is smaller than the quantity of the copper.

3(original). The structure of claim 1, wherein the first barrier layer is a nickel-vanadium layer.

4(original). The structure of claim 1, wherein the wetting layer is a copper layer.

5(original). The structure of claim 1, wherein the wetting layer is a nickel layer.

6(original). The structure of claim 1, wherein the wetting layer is a titanium layer.

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7(original). The structure of claim 1, wherein the thickness of the second barrier layer is ranged from about 50  $\mu\text{m}$  to about 80  $\mu\text{m}$ .

Claims 8-19(canceled).